

#### **Description**

The AR0541D3 is a 5V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR0541D3 has a low capacitance with a typical value at 0.6pF, and complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge protection make AR0541D3 an ideal choice to protect cell phone, wireless systems, and communication equipment.

### **Features**

200W peak pulse power (8/20µs)

• Ultra low capacitance: 0.6pF typical

Ultra low leakage: nA level

Operating voltage: 5V

Low clamping voltage

· Protects one power line or data line

· Complies with following standards:

IEC 61000-4-2 (ESD) immunity test
Air discharge: ±30kV

Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 8A (8/20µs)

RoHS Compliant

#### **Mechanical Characteristics**

Package: SOD-323Lead Finish: Matte Tin

Case Material: "Green" Molding Compound.Terminal Connections: See Diagram Below

Marking Information: See Below

### **Applications**

USB Ports

Smart Phones

Wireless Systems

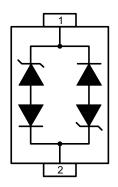
Ethernet 10/100/1000 Base T

### **Marking Information**



### **Ordering Information**

### **Dimensions and Pin Configuration**



Circuit and Pin Schematic

Part Number	Packaging	Reel Size
AR0541D3	3000/Tape & Reel	7 inch



## Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise specified)

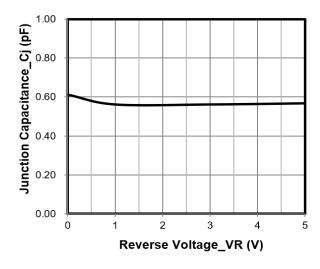
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	200	W
Peak Pulse Current (8/20µs)	IPP	8	Α
ESD per IEC 61000-4-2 (Air)	VESD	±30	kV
ESD per IEC 61000-4-2 (Contact)	VESD	±30	N.V
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C

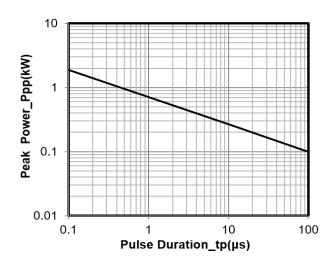
# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	٧	
Breakdown Voltage	VBR	6		9	V	IT = 1mA
Reverse Leakage Current	I <sub>R</sub>			0.2	μA	VRWM = 5V
Clamping Voltage	Vc			12	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	Vc			25	V	IPP = 8A (8 x 20μs pulse)
Junction Capacitance	Сл		0. 6		pF	VR = 0V, f = 1MHz



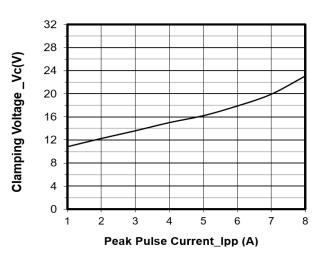
### Typical Performance Characteristics (TA=25°C unless otherwise Specified)

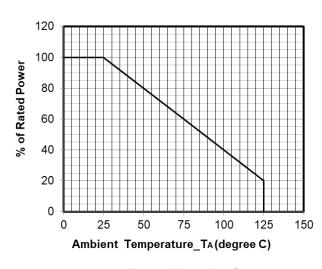




Junction Capacitance vs. Reverse Voltage

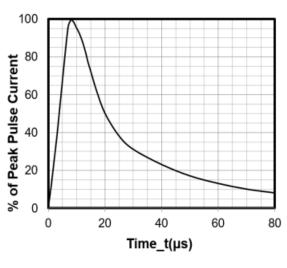
Peak Pulse Power vs. Pulse Time

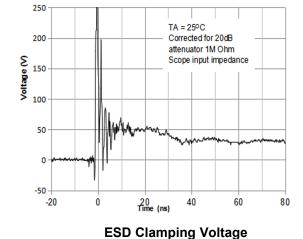




Clamping Voltage vs. Peak Pulse Current

**Power Derating Curve** 



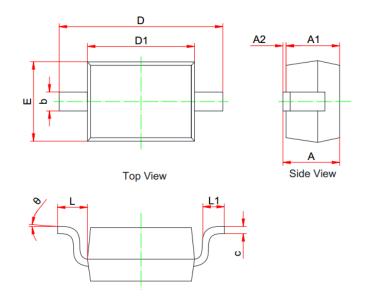


8 X 20µs Pulse Waveform

8 kV Contact per IEC61000-4-2



### **SOD-323 Package Outline Drawing**



	MILLIMETERS					
SYM	MIN	NOM	MAX			
Α	0.800		1.100			
A1	0.800		0.900			
A2	0.000		0.100			
b	0.250		0.400			
С	0.080		0.177			
D1	1.600	1.700	1.800			
D	2.300		2.800			
Е	1.150		1.400			
L	0.475REF					
L1	0.100		0.500			
Θ	0°		8°			

## **Suggested Land Pattern**



Unit: mm

## **Contact Information**

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